

ESD9B5V

Ultra Small Profile, Bidirectional Transient Voltage Suppressor

[Http://www.willsemi.com](http://www.willsemi.com)

Descriptions

The ESD9B5V is an ESD transient voltage suppression component which provides a very high level of protection for sensitive electronic components that may be subjected to electrostatic discharge (ESD). It is particularly well-suited for cellular phones, portable device, digital cameras, power supplies and many other portable applications because of its small package and low weight.

The ESD9B5V is Bidirectional, Safely dissipate ESD strikes of Level 4, IEC61000-4-2, exceeding the maximum requirement. Using the MILSTD-883 (Method 3015) specification for Human Body Model (HBM) ESD, the device provides protection for contact discharges to greater than +/-15KV.

The ESD9B5V is available in a WBFBP-02C package with peak reverse working voltage of 5 voltages.

Features

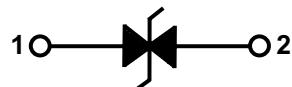
- Peak Reverse Working Voltage: 5V
- Peak power up to 100W @ 8 x 20 us Pulse
- Low leakage current
- High ESD protection Level: >+/-15KV per HBM
- IEC61000-4-2 Level 4 ESD Protection
- IEC61000-4-4 Level 4 EFT Protection
- Small Body Outline: 1.0 x 0.6 x 0.5mm

Applications

- Cell phone handsets and accessories
- Personal Digital Assistants (PDAs)
- Notebooks, Desktops, and Servers
- Portable Instrumentation
- Digital Cameras
- MP3/MP4/PMP Players



Package Diagram



Pin Configuration



EB = Special Device Code

Marking Diagram and explain

Order Information

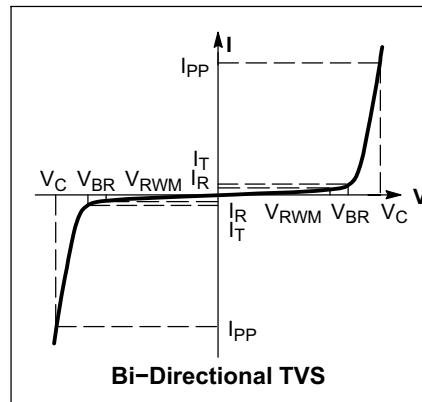
Device	Package	Shipping
ESD9B5V-2/TR	WBFBP-02C	5000/Tape&Reel

Maximum Ratings

Rating	Symbol	Value	Units
Peak pulse power ($t_p=8/20\text{ }\mu\text{s}$)	Ppk	100	W
Maximum peak pulse current ($t_p=8/20\text{ }\mu\text{s}$)	Ipp	8.7	A
ESD Per IEC61000-4-2 (Air)	Vpp	+/-15	kV
ESD Per IEC61000-4-2 (Contact)		+/-8	
Maximum lead temperature for soldering during 10s	T _L	260	°C
Storage temperature range	T _{stg}	-55 to +150	°C
Operating temperature range	T _{op}	-55 to +150	°C

Electronics Parameter

Symbol	Parameter
V _{rwm}	Peak Reverse Working Voltage
I _r	Reverse Leakage Current @ V _{rwm}
V _{br}	Breakdown Voltage @ I _t
I _t	Test Current
I _{pp}	Maximum Reverse Peak Pulse Current
V _c	Clamping Voltage @ I _{pp}
P _{pk}	Peak Power Dissipation
C	Junction Capacitance
I _f	Forward Current
V _f	Forward Voltage @ I _f



Electronics Characteristics

Device	Marking	V _{rwm} (V)	I _r (uA) @ V _{rwm}	V _{br} (V) @ I _t (Note1)	I _t (mA)	I _{pp} (A)	V _c (V) @ Max I _{pp}	P _{pk} (W) (8 x 20us) (Note2)	C (pF)
		Max.	Max.	Min.	Typ.	Max.	Max.	Typ.	Typ.
ESD9B5V-2/TR	EB	5.0	0.5	7.5	1	8.7	12.5	100	30

Note 1: V_{br} is measured with a pulse current I_t.

Note 2: Surge current waveform per Figure 1.

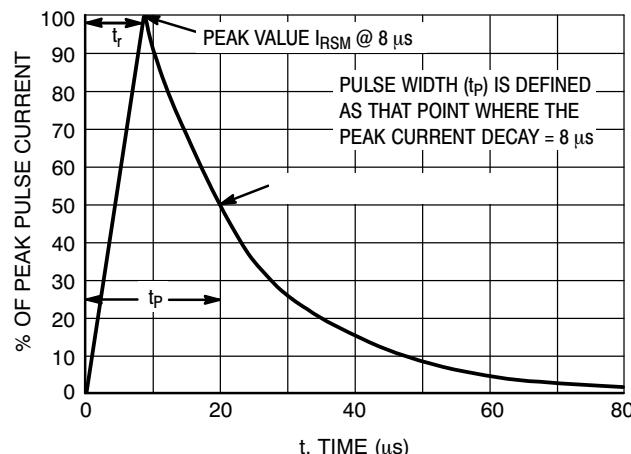


Figure1. 8x20us pulse waveform

Typical Performance Graph

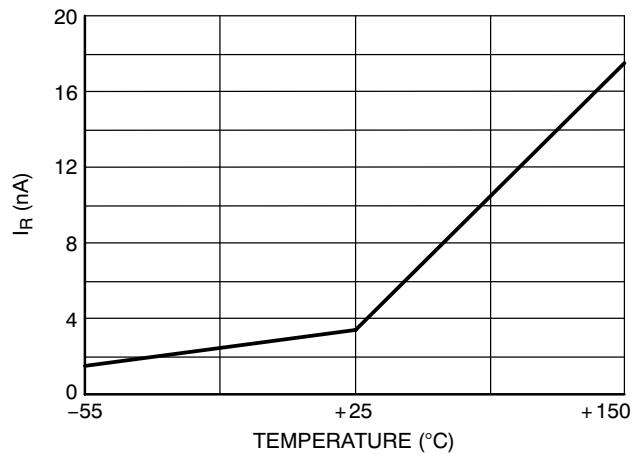
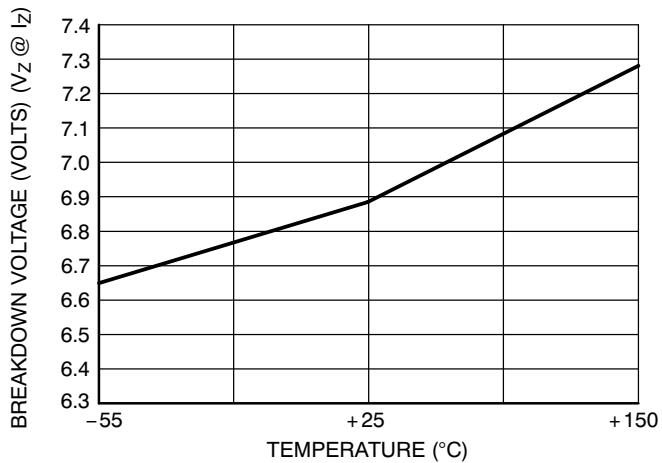
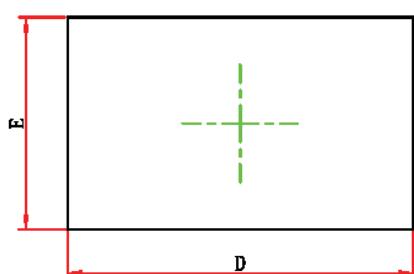
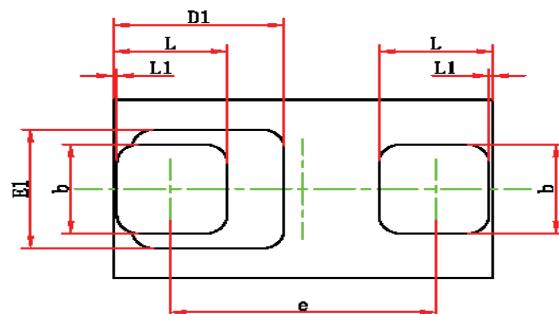
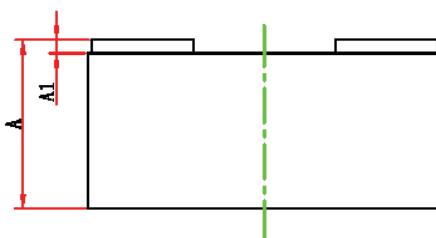


Figure2. Typical breakdown voltage vs temperature

Figure3. Typical leakage current vs temperature

Outline Dimension

Top View

Bottom View

Side View

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.450	0.550	0.018	0.022
A1	0.010	0.070	0.000	0.003
D	0.95	1.050	0.037	0.011
E	0.550	0.650	0.022	0.026
D1	0.450REF		0.018REF	
E1	0.400REF		0.016REF	
b	0.275	0.325		0.013
e	0.675	0.725		0.029
L	0.275	0.325		0.013
L1	0.010REF		0.000REF	

